



Op 2812

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chandra V. Mouli § Group Art Unit: 2812  
Serial No.: 09/379,092 §  
Filed: August 23, 1999 § Examiner: R. Pompey  
For: FORMING SIDEWALL OXIDE §  
LAYERS FOR TRENCH §  
ISOLATION § Atty. Dkt. No.: MICT-0042-US

8/a  
G. Stanley  
4-27-01

Commissioner for Patents  
Washington DC 20231

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REPLY TO PAPER NO. 7

Sir:

In response to the office action mailed March 28, 2001,  
please amend the above-referenced patent application as follows:

In the Claims:

Please amend claim 1 as follows:

1. (Amended) A method of forming a trench isolation  
comprising:  
forming a region containing oxidation enhancing  
impurities in a semiconductor structure by implanting impurities  
which enhance the oxidation of said structure beyond that which  
would be expected from crystallographic damage effects; and  
making a trench through said region, leaving a portion  
of said region around said trench.

Please cancel claim 4.

Please amend claim 5 as follows:

5. (Amended) The method of claim 1 further including  
implanting argon.

[Please amend claim 6 as follows:]

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Lisa O'Sullivan